

✓ 28. The semiconductor structure of Claim 19, wherein the conductive element is a gate electrode.

✓ 29. The semiconductor structure of Claim 28, further comprising a gate dielectric layer located between the semiconductor substrate and the gate electrode.

✓ 30. The semiconductor structure of Claim 19, further comprising a source/drain region located in the semiconductor substrate, wherein the silicide strap contacts the source/drain region.

✓ 31. The semiconductor structure of Claim 19, wherein the dielectric spacer comprises silicon oxide or silicon nitride.

✓ 32. The semiconductor structure of Claim 19, wherein the silicide strap comprises cobalt silicide.

✓ 33. The semiconductor structure of Claim 21, wherein the silicide strap comprises a refractory metal layer reacted with the semiconductor region.

✓ 34. The semiconductor structure of Claim 21, wherein the conductive element is a gate electrode.

✓ 35. The semiconductor structure of Claim 34, further comprising a gate dielectric layer located between the semiconductor substrate and the gate electrode.

✓ 36. The semiconductor structure of Claim 21, further comprising a source/drain region located in the

semiconductor substrate, wherein the silicide strap contacts the source/drain region.

*C' cont*

37. The semiconductor structure of Claim 21, wherein the dielectric spacer comprises silicon oxide or silicon nitride.

*D' cont*

38. The semiconductor structure of Claim 21, wherein the silicide strap comprises cobalt silicide.--